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TITLE : METHOD FOR FORMATION OF III-GROUP ELEMENT NITRIDE FILM

ABSTRACT : PURPOSE: To effectively form a nitride film by effectively cracking ammonia at a relatively low temperature.

CONSTITUTION: A surface of a GaAs substrate heated is turned into a Ga saturated face. A cracking cell filled with alumina fibers is heated to 300-550°C, and ammonia gas is passed therethrough. Ammonia gas, cracked using alumina fibers as catalyst, reacts with Ga in the Ga saturated face, a GaN film being formed.

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